

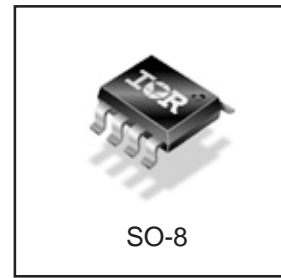
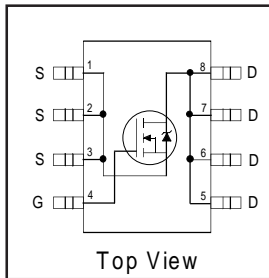
**Applications**

- High Frequency Isolated DC-DC Converters with Synchronous Rectification for Telecom and Industrial Use
- High Frequency Buck Converters for Computer Processor Power

$V_{DSS}$	$R_{DS(on)}$ max(m $\Omega$ )	$I_D$
<b>20V</b>	<b>10@<math>V_{GS} = 10V</math></b>	<b>12A</b>

**Benefits**

- Ultra-Low Gate Impedance
- Very Low  $R_{DS(on)}$
- Fully Characterized Avalanche Voltage and Current



**Absolute Maximum Ratings**

Symbol	Parameter	Max.	Units
$V_{DS}$	Drain-Source Voltage	20	V
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	12	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	10	
$I_{DM}$	Pulsed Drain Current <sup>①</sup>	100	
$P_D @ T_A = 25^\circ C$	Maximum Power Dissipation <sup>③</sup>	2.5	W
$P_D @ T_A = 70^\circ C$	Maximum Power Dissipation <sup>③</sup>	1.6	W
	Linear Derating Factor	0.02	mW/ $^\circ C$
$T_J, T_{STG}$	Junction and Storage Temperature Range	-55 to + 150	$^\circ C$

**Thermal Resistance**

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JL}$	Junction-to-Drain Lead	—	20	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient <sup>⑤</sup>	—	50	

Notes <sup>①</sup> through <sup>⑤</sup> are on page 8

# IRF7460

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## Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	20	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.089	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	7.2	10	m $\Omega$	$V_{GS} = 10V, I_D = 12A$ ④
		—	10.5	14		$V_{GS} = 4.5V, I_D = 9.6A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	3.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	20	$\mu A$	$V_{DS} = 16V, V_{GS} = 0V$
		—	—	100		$V_{DS} = 16V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -16V$

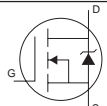
## Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$g_{fs}$	Forward Transconductance	26	—	—	S	$V_{DS} = 16V, I_D = 9.6A$
$Q_g$	Total Gate Charge	—	19	—	nC	$I_D = 9.6A$
$Q_{gs}$	Gate-to-Source Charge	—	6.9	—		$V_{DS} = 10V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	6.0	—		$V_{GS} = 4.5V,$ ④
$Q_{oss}$	Output Gate Charge	—	17	26		$V_{GS} = 0V, V_{DS} = 10V$
$t_{d(on)}$	Turn-On Delay Time	—	11	—	ns	$V_{DD} = 10V$
$t_r$	Rise Time	—	6.9	—		$I_D = 9.6A$
$t_{d(off)}$	Turn-Off Delay Time	—	12	—		$R_G = 1.8\Omega$
$t_f$	Fall Time	—	4.3	—		$V_{GS} = 4.5V$ ④
$C_{iss}$	Input Capacitance	—	2050	—		$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	1060	—	$V_{DS} = 10V$	
$C_{riss}$	Reverse Transfer Capacitance	—	150	—	pF	$f = 1.0\text{MHz}$

## Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
$E_{AS}$	Single Pulse Avalanche Energy②	—	240	mJ
$I_{AR}$	Avalanche Current①	—	9.6	A

## Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	2.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	100		
$V_{SD}$	Diode Forward Voltage	—	0.8	1.3	V	$T_J = 25^\circ\text{C}, I_S = 9.6A, V_{GS} = 0V$ ④
		—	0.66	—		$T_J = 125^\circ\text{C}, I_S = 9.6A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	—	44	66	ns	$T_J = 25^\circ\text{C}, I_F = 9.6A, V_R = 10V$
$Q_{rr}$	Reverse Recovery Charge	—	60	90	nC	$di/dt = 100A/\mu s$ ④
$t_{rr}$	Reverse Recovery Time	—	44	66	ns	$T_J = 125^\circ\text{C}, I_F = 9.6A, V_R = 10V$
$Q_{rr}$	Reverse Recovery Charge	—	64	96	nC	$di/dt = 100A/\mu s$ ④

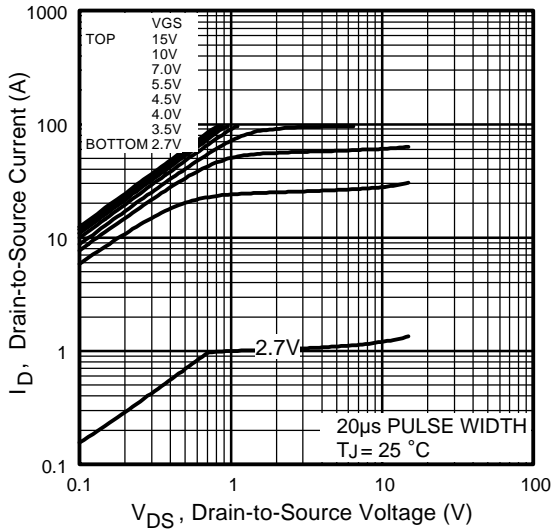


Fig 1. Typical Output Characteristics

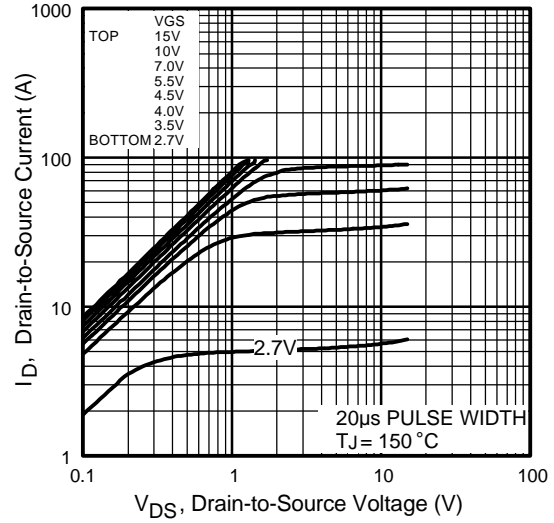


Fig 2. Typical Output Characteristics

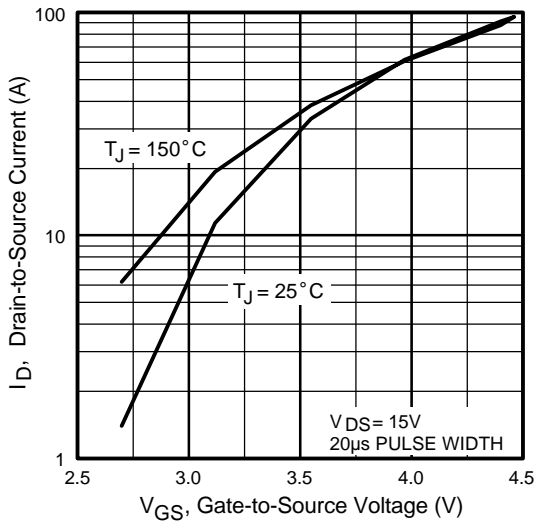


Fig 3. Typical Transfer Characteristics

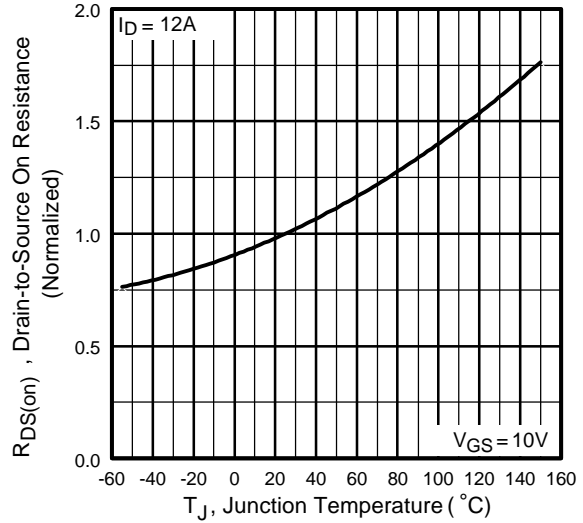
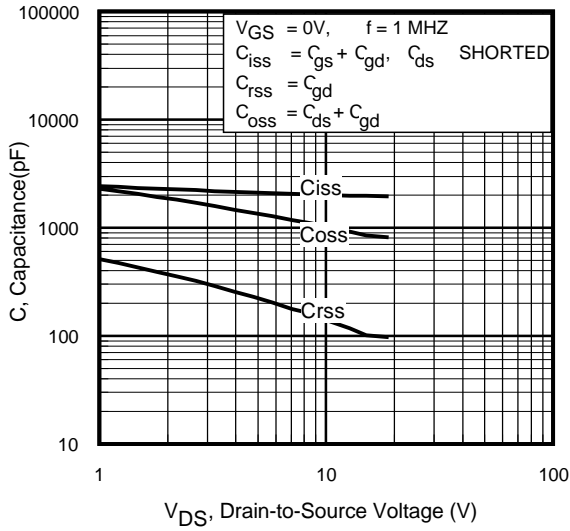
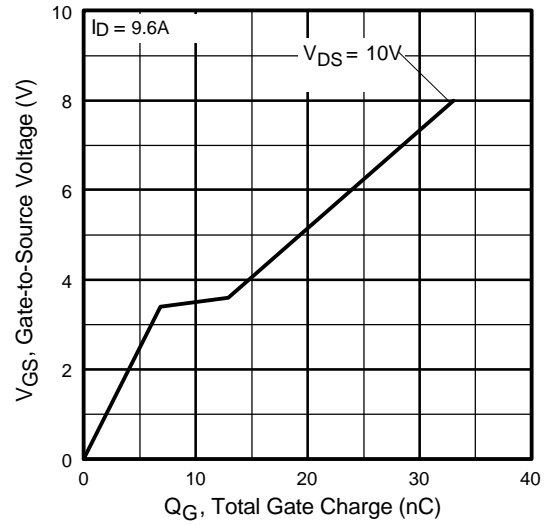


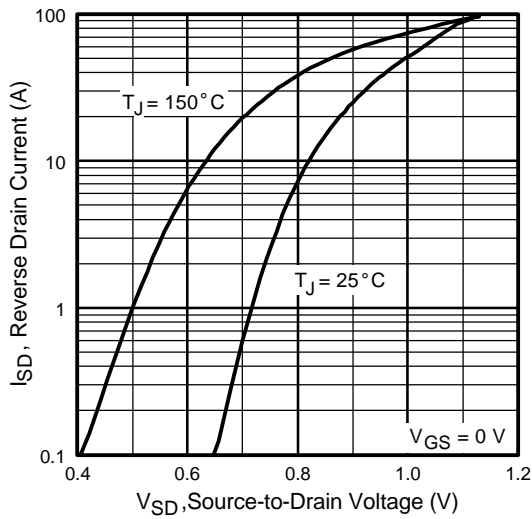
Fig 4. Normalized On-Resistance Vs. Temperature



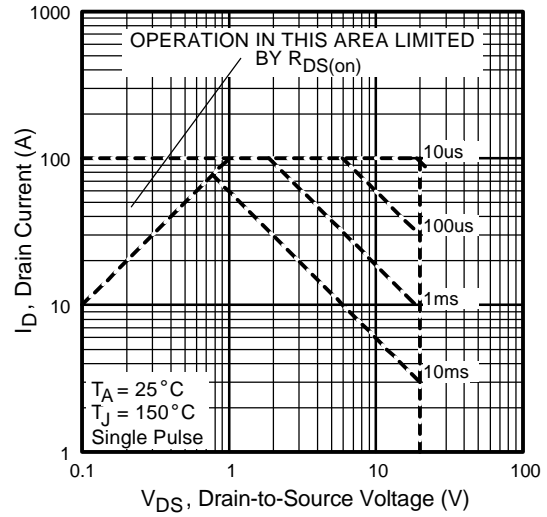
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage

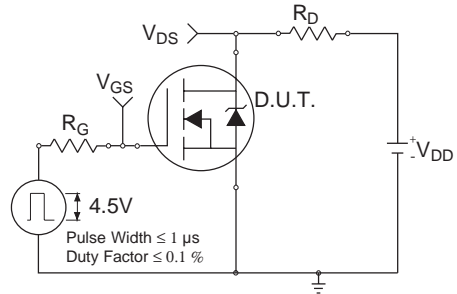
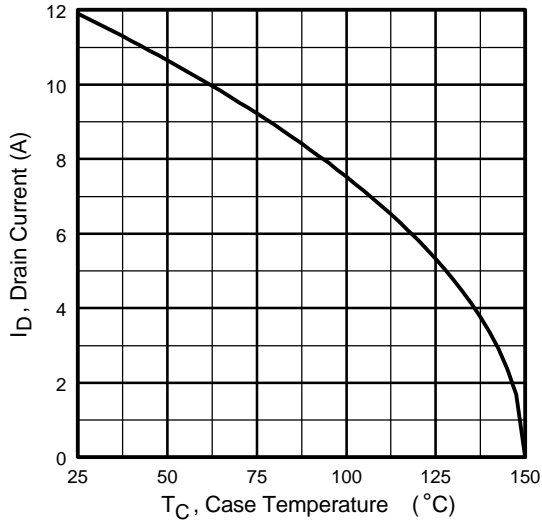


**Fig 7.** Typical Source-Drain Diode Forward Voltage

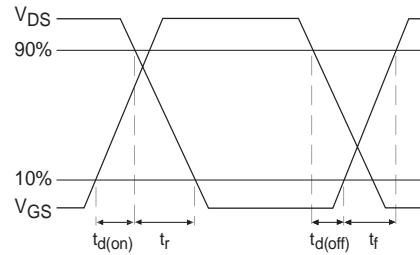


**Fig 8.** Maximum Safe Operating Area

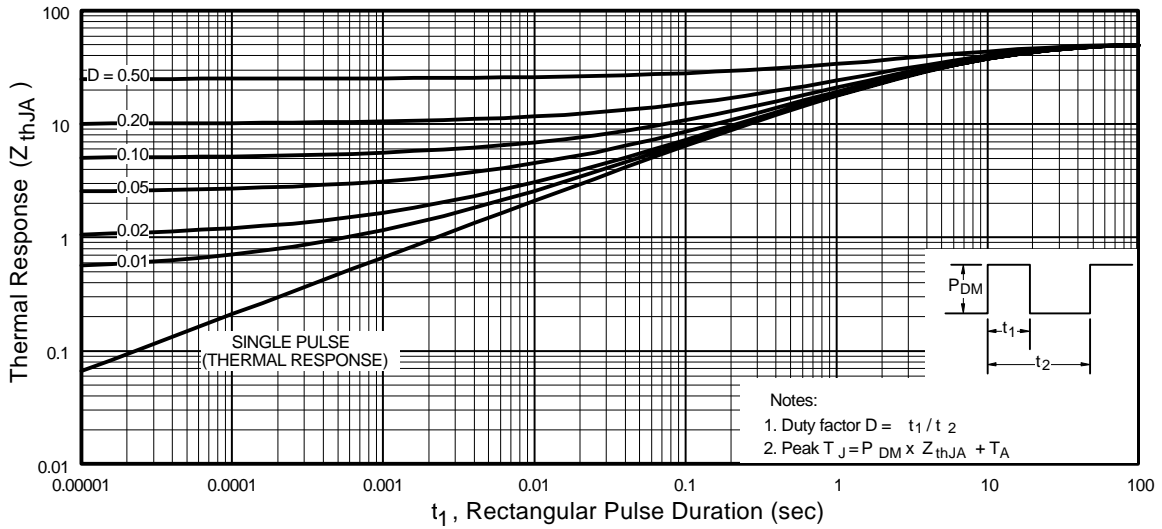
**Fig 6. On-Resistance Vs. Drain Current**



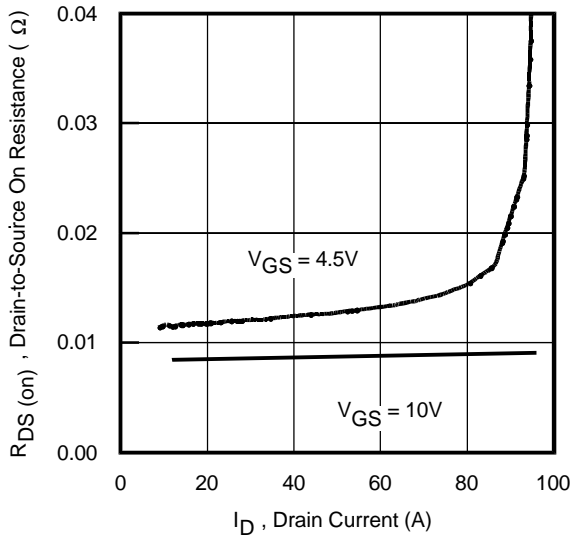
**Fig 10a. Switching Time Test Circuit**



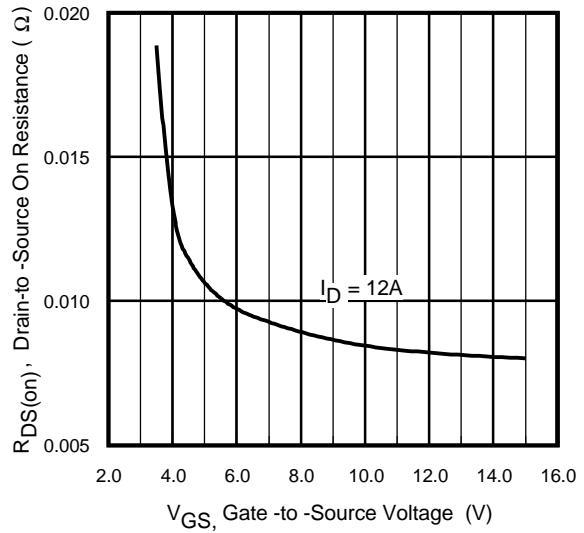
**Fig 10b. Switching Time Waveforms**



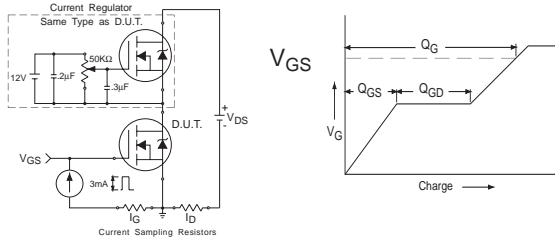
**Fig 10. Maximum Effective Transient Thermal Impedance, Junction-to-Case**



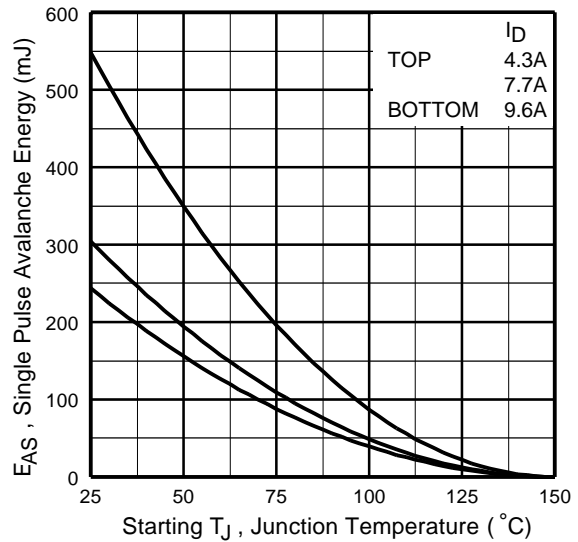
**Fig 12.** On-Resistance Vs. Drain Current



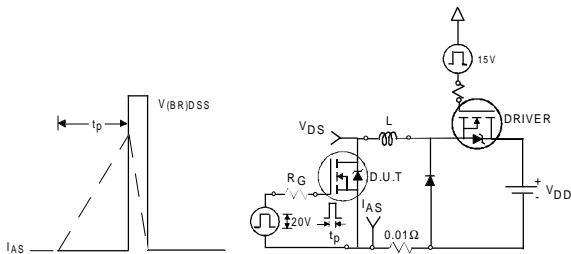
**Fig 13.** On-Resistance Vs. Gate Voltage



**Fig 13a&b.** Basic Gate Charge Test Circuit and Waveform

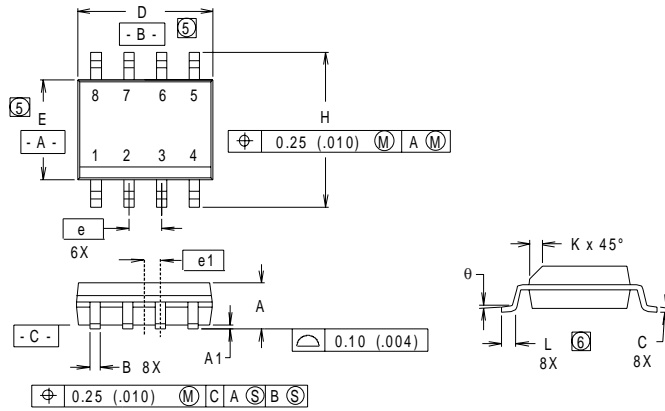


**Fig 14c.** Maximum Avalanche Energy Vs. Drain Current



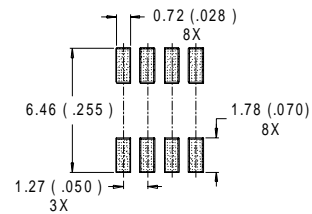
**Fig 14a&b.** Unclamped Inductive Test circuit and Waveforms

## SO-8 Package Details



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
B	.014	.018	0.36	0.46
C	.0075	.0098	0.19	0.25
D	.189	.196	4.80	4.98
E	.150	.157	3.81	3.99
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.011	.019	0.28	0.48
L	0.16	.050	0.41	1.27
$\theta$	0°	8°	0°	8°

### RECOMMENDED FOOTPRINT

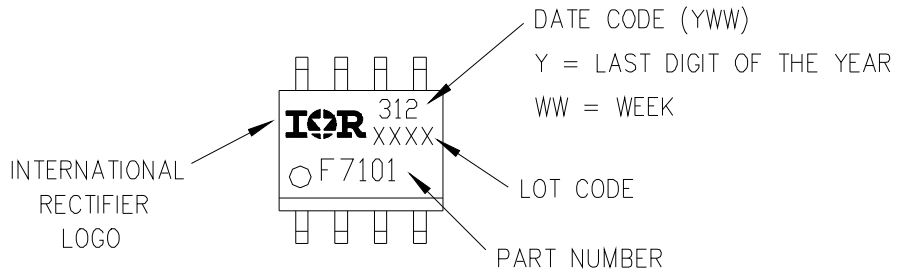


### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSII Y14.5M-1982.
2. CONTROLLING DIMENSION : INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- (5) DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS  
MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.006).
- (6) DIMENSIONS IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE..

## SO-8 Part Marking

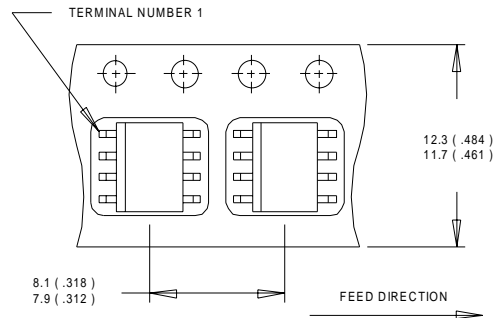
EXAMPLE: THIS IS AN IRF7101



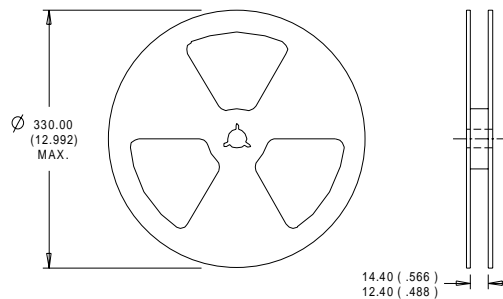
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## SO-8 Tape and Reel



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
  2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
  3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
  2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 5.2\text{mH}$   
 $R_G = 25\Omega$ ,  $I_{AS} = 9.6\text{A}$ .
- ③ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ④ When mounted on 1 inch square copper board,  $t < 10$  sec

Data and specifications subject to change without notice.  
This product has been designed and qualified for the Industrial market.  
Qualification Standards can be found on IR's Web site.

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**IR** Rectifier

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